



CST10N15 N-Ch 150V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

CST10N15 Product Summary



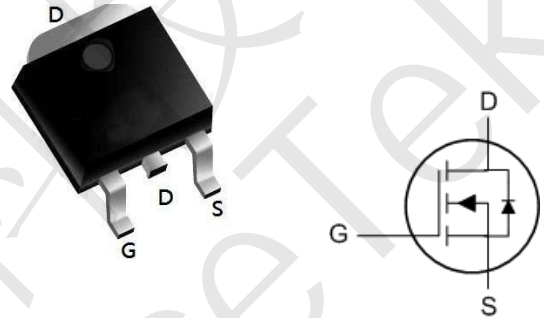
BVDSS	RDSON	ID
150V	240mΩ	10A

CST10N15 Description

The CST10N15 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The CST10N15 meet the RoHS and Green Product requirement with full function reliability approved.

CST10N15 TO252 Pin Configuration



7 GH%\$B%) '5 Vgc`i h'AU]a i a 'FU]b[g`fh5 '1'8) š7 zi b'Ygg'ch Yfk IgY'bcHXL

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	10
		$T_C=100^{\circ}C$	5.4
Pulsed Drain Current ¹	I_{DM}	35	A
Single Pulse Avalanche Energy ²	EAS	9.8	mJ
Total Power Dissipation	P_D	40.3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	62	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	3.1	°C/W



CST10N15 N-Ch 150V Fast Switching MOSFETs

CST10N15 Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	150	-	-	V
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 150V, V _{GS} = 0V	T _J =25°C	-	1	μA
			T _J =100°C	-	100	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	2	2.5	V
Drain-Source on-Resistance ⁴	R _{DS(on)}	V _{GS} = 10V, I _D = 4A	-	240	300	mΩ
Forward Transconductance ⁴	g _{fs}	V _{DS} = 10V, I _D = 4A	-	14.5	-	S
Dynamic Characteristics⁵						
Input Capacitance	C _{iss}	V _{DS} = 75V, V _{GS} = 0V, f = 1MHz	-	465	-	pF
Output Capacitance	C _{oss}		-	23	-	
Reverse Transfer Capacitance	C _{rss}		-	14	-	
Gate Resistance	R _g	f = 1MHz	-	2	-	Ω
Switching Characteristics⁵						
Total Gate Charge	Q _g	V _{GS} = 10V, V _{DS} = 75V, I _D = 4A	-	14	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	
Gate-Drain Charge	Q _{gd}		-	4	-	
Turn-on Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 75V, R _G = 3Ω, I _D = 4A	-	5.8	-	ns
Rise Time	t _r		-	2.2	-	
Turn-off Delay Time	t _{d(off)}		-	16.9	-	
Fall Time	t _f		-	2.6	-	
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	I _S	T _C = 25°C	-	-	10	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The EAS data shows Max. rating. The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.4mH, I_{AS} = 7A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.



CST10N15 Typical Characteristics

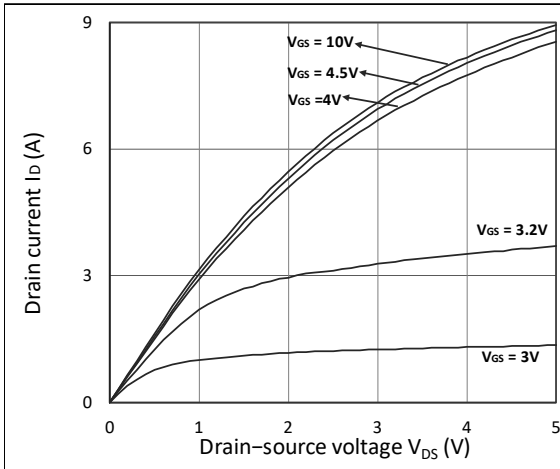


Figure 1. Output Characteristics

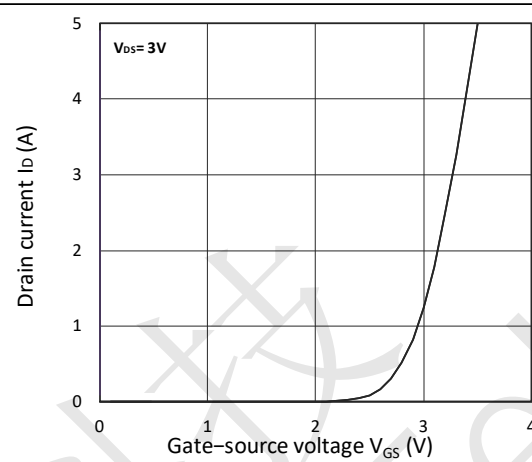


Figure 2. Transfer Characteristics

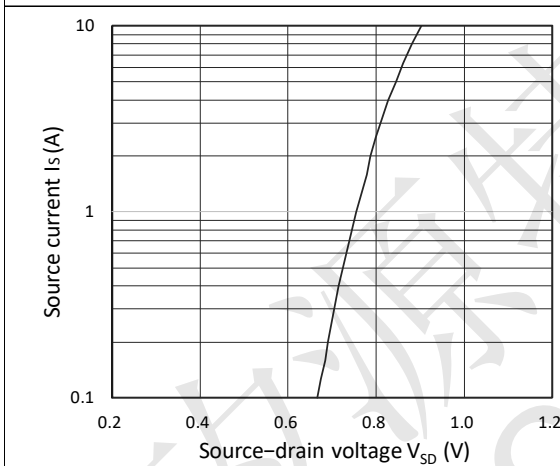


Figure 3. Forward Characteristics of Reverse

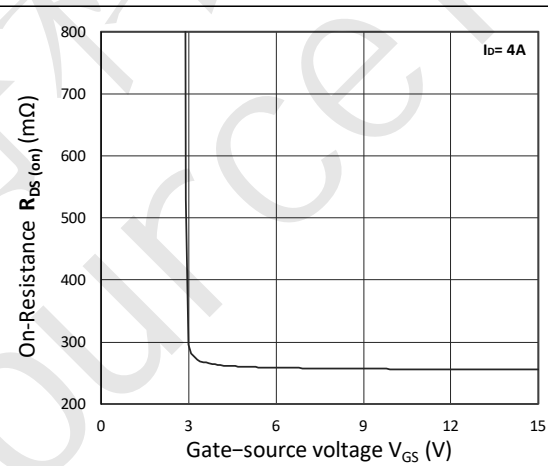


Figure 4. $R_{DS(on)}$ vs. V_{GS}

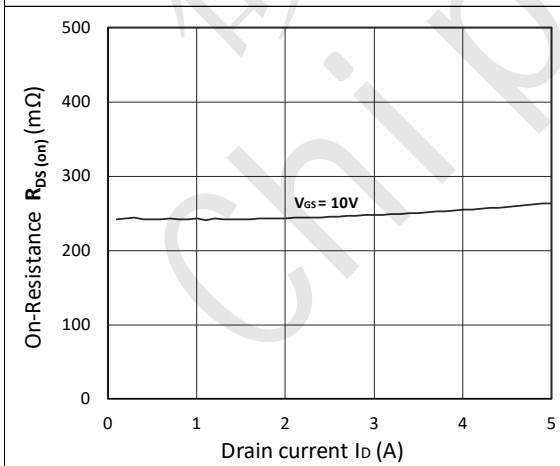


Figure 5. $R_{DS(on)}$ vs. I_D

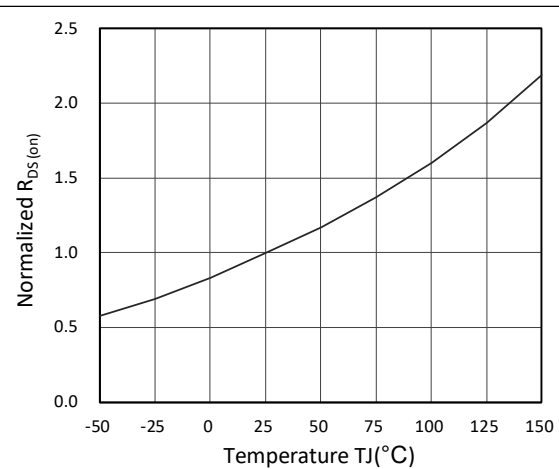


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature



CST10N15 N-Ch 150V Fast Switching MOSFETs

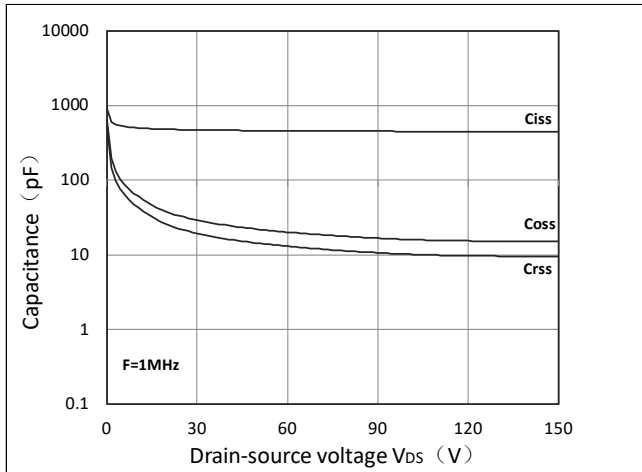


Figure 7. Capacitance Characteristics

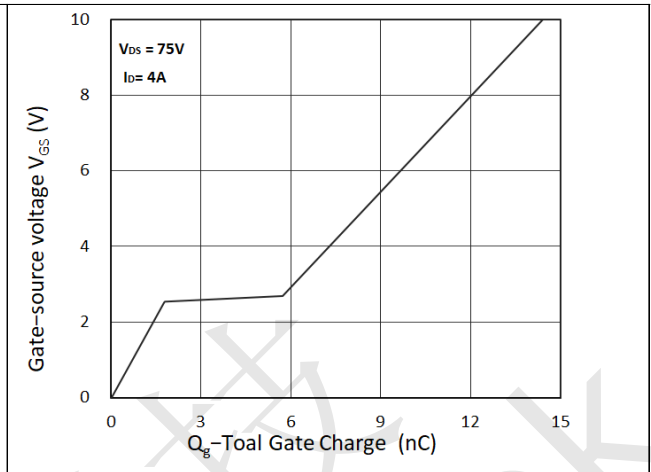


Figure 8. Gate Charge Characteristics

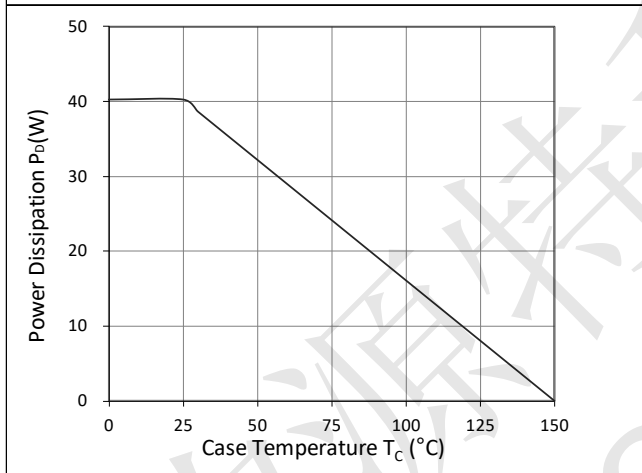


Figure 9. Power Dissipation

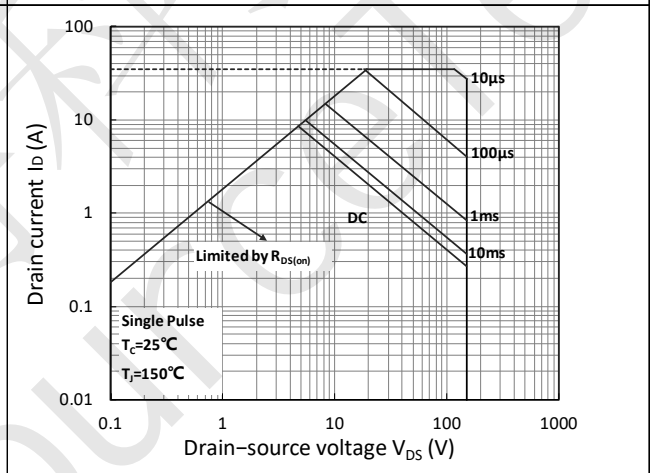


Figure 10. Safe Operating Area

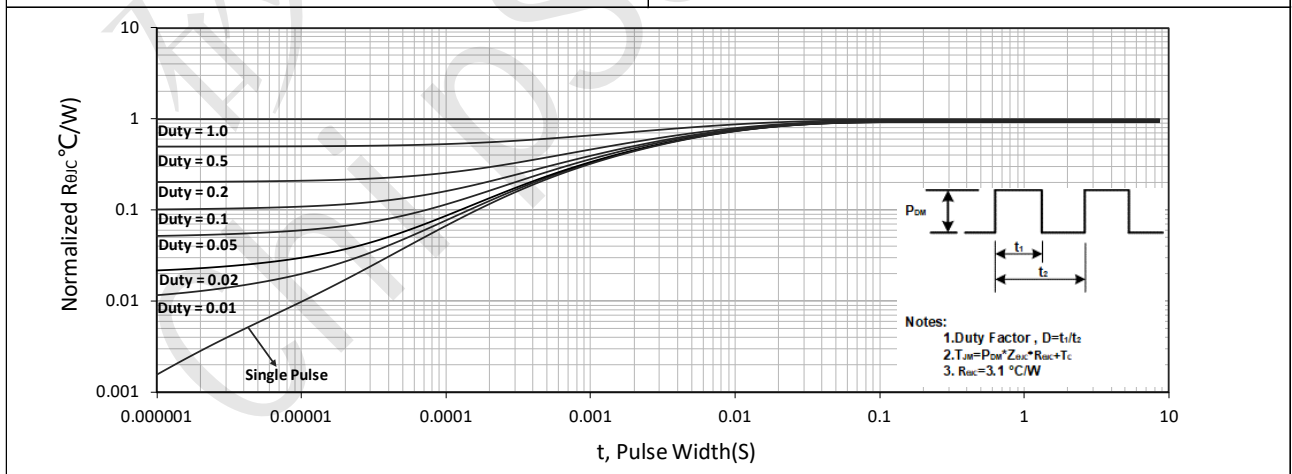
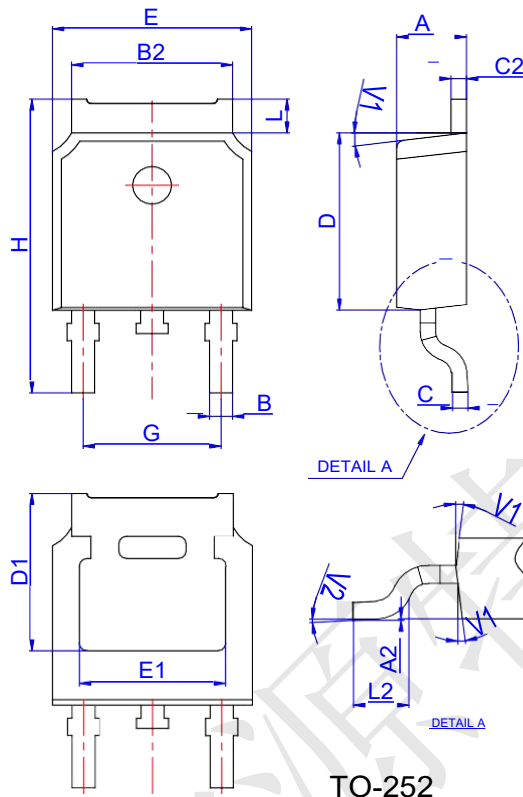


Figure 11. Normalized Maximum Transient Thermal Impedance

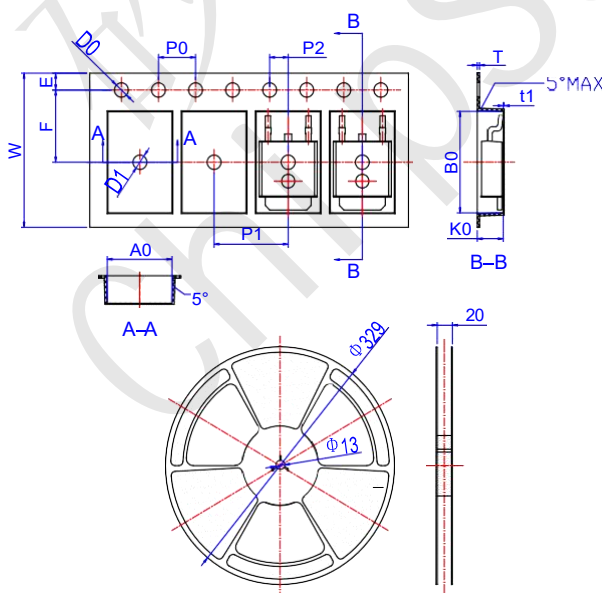


CST10N15 Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583